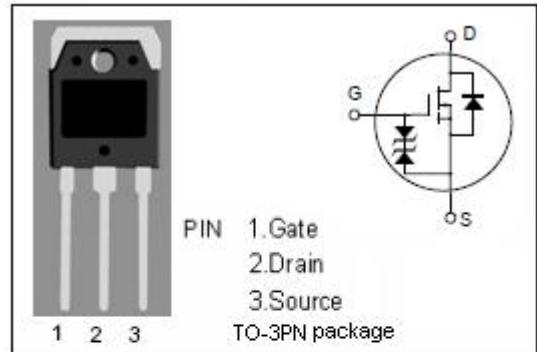


## isc N-Channel MOSFET Transistor

2SK1933

**DESCRIPTION**

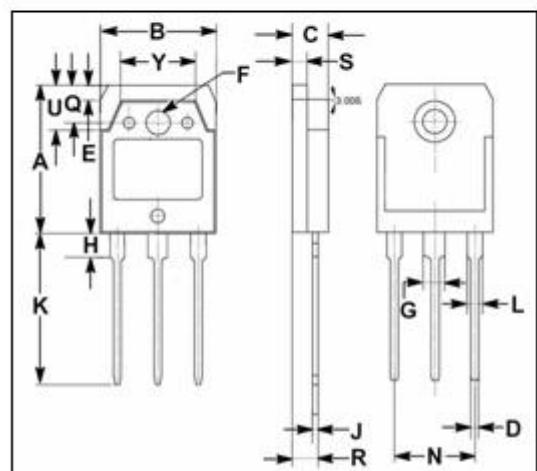
- Drain Current – $I_D=10A$ @  $T_C=25^\circ C$
- Drain Source Voltage-
  - :  $V_{DSS}= 900V$ (Min)
- Fast Switching Speed
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

**APPLICATIONS**

- Suitable for switching regulator

**ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ C$ )**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{DSS}$	Drain-Source Voltage ( $V_{GS}=0$ )	900	V
$V_{GS}$	Gate-Source Voltage	$\pm 30$	V
$I_D$	Drain Current-continuous@ $TC=25^\circ C$	10	A
$P_{tot}$	Total Dissipation@ $TC=25^\circ C$	150	W
$T_j$	Max. Operating Junction Temperature	150	°C
$T_{stg}$	Storage Temperature Range	-55~150	°C



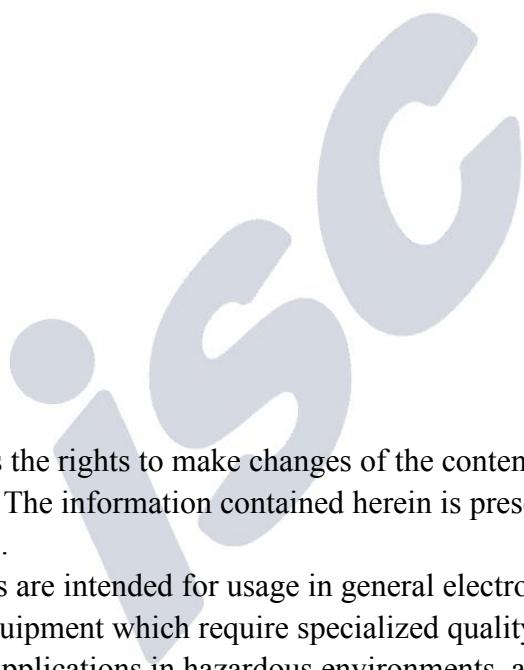
DIM	mm	
	MIN	MAX
A	19.60	20.10
B	15.50	15.70
C	4.70	4.90
D	0.90	1.10
E	1.90	2.10
F	3.40	3.60
G	2.90	3.20
H	3.20	3.40
J	0.595	0.605
K	20.00	20.70
L	1.90	2.20
N	10.89	10.91
Q	4.90	5.10
R	3.35	3.45
S	1.995	2.100
U	5.90	6.10
Y	9.90	10.10

## isc N-Channel Mosfet Transistor

2SK1933

• ELECTRICAL CHARACTERISTICS ( $T_c=25^\circ\text{C}$ )

SYMBOL	PARAMETER	CONDITIONS	MIN	TYPE	MAX	UNIT
$V_{(\text{BR})\text{DSS}}$	Drain-Source Breakdown Voltage	$V_{\text{GS}}= 0$ ; $I_D= 10\text{mA}$	900			V
$V_{(\text{BR})\text{GSS}}$	Gate-Source Breakdown Voltage	$V_{\text{DS}}= 0$ ; $I_G= 100 \mu\text{A}$	$\pm 30$			V
$V_{\text{GS}(\text{th})}$	Gate Threshold Voltage	$V_{\text{DS}}= 10\text{V}$ ; $I_D= 1\text{mA}$	2		3	V
$V_{\text{DF}}$	Body to drain diode forward voltage	$I_F= 10 \text{ A}$ , $V_{\text{GS}}= 0$		0.9		V
$R_{\text{DS}(\text{on})}$	Drain-Source On-Resistance	$V_{\text{GS}}= 10\text{V}$ ; $I_D= 5\text{A}$		0.9	1.2	$\Omega$
$I_{\text{GSS}}$	Gate-Body Leakage Current	$V_{\text{GS}}= \pm 25\text{V}$ ; $V_{\text{DS}}= 0$			$\pm 10$	$\mu\text{A}$
$I_{\text{DSS}}$	Zero Gate Voltage Drain Current	$V_{\text{DS}}= 720\text{V}$ ; $V_{\text{GS}}= 0$			250	$\mu\text{A}$
$C_{\text{iss}}$	Input capacitance	$V_{\text{DS}}= 10\text{V}$ ; $V_{\text{GS}}= 0\text{V}$ ; $f_T= 1\text{MHz}$		2620		pF
$C_{\text{rss}}$	Reverse transfer capacitance			320		
$C_{\text{oss}}$	Output capacitance			830		
$t_r$	Rise time	$V_{\text{GS}}= 10\text{V}$ ; $I_D= 5\text{A}$ ; $V_{\text{DD}}= 200\text{V}$ ; $R_L= 6 \Omega$		140		ns
$t_{\text{on}}$	Turn-on time			30		
$t_f$	Fall time			170		
$t_{\text{off}}$	Turn-off time			285		

A large, semi-transparent watermark of the "isc" logo, where the letters are stylized and slanted upwards. It is positioned diagonally across the page.**NOTICE:**

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